

a semiconductor substrate;

a plurality of first active regions formed on the semiconductor substrate;

a plurality of gates formed in each of the first active regions;

b1
at least one second active region of a predetermined conductive type formed additionally between the first active regions, wherein the second active region includes an n+ junction connected to Vcc reference voltage or a p+ junction connected to ground Vss, and is without a gate, a source and a drain; and

a third active region surrounding the first and second active regions and being of conductivity type different from that of the first active regions.

b2
7. (Amended) The device of claim 1, further comprising:

a plurality of source regions each formed between a pair of gates in each of the first active regions.

b3
11. (Twice Amended) A multi-finger type ESD protection device comprising:

a semiconductor substrate;

a plurality of first active regions formed separately on the semiconductor substrate;

a plurality of gates formed in each of the first active regions; and

b3
at least one predetermined conductive type second active region formed between two of the first active regions, wherein the predetermined conductive type second active region includes an n+ junction connected to Vcc reference voltage, and is without a gate, a source and a drain.

18. (Twice Amended) A multi-finger type ESD protection device comprising:

a semiconductor substrate;

b4
a plurality of first active regions formed separately on the semiconductor substrate;

a plurality of gates formed in each of the first active regions;

at least one second active region of a predetermined conductive type, formed between the first active regions, wherein the predetermined conductive type second active region includes a p+ junction connected to ground Vss, and is without a gate, a source and a drain; and

a third active region surrounding the first and second active regions and being of conductivity type different from that of the first active regions.

b5
22. (Amended) The device of claim 21, wherein the third active region has a ring configuration.

Please add the following claims.

--28. (NEW) A multi-finger type ESD protection device comprising:

a semiconductor substrate;

a plurality of first active regions formed on the semiconductor substrate;

a plurality of gates formed in each of the first active regions;

at least one second active region of a predetermined conductive type

formed additionally between the first active regions, wherein the second active

region includes an n+ junction connected to Vcc reference voltage or a p+

junction connected to ground Vss;

a third active region surrounding the first and second active regions and

being of conductivity type different from that of the first active regions; and

a plurality of drain regions formed in each of the first active regions,

wherein the drain regions include a pair of drain regions formed at n+

junctions of both end portions of each of the first active regions.

29. (NEW) A multi-finger type ESD protection device comprising:

a semiconductor substrate;

a plurality of first active regions formed separately on the semiconductor

substrate;

a plurality of gates formed in each of the first active regions;

at least one predetermined conductive type second active region formed between two of the first active regions, wherein the predetermined conductive type second active region is an n+ junction connected to Vcc reference voltage; and

drain regions formed at n+ junctions of both end portions of the first active regions.

30. (NEW) A multi-finger type ESD protection device comprising:

a semiconductor substrate;

A (in) a plurality of first active regions formed separately on the semiconductor substrate;

a plurality of gates formed in each of the first active regions;

at least one second active region of a predetermined conductive type, formed between the first active regions, wherein the predetermined conductive type second active region includes a p+ junction connected to ground Vss;

a third active region surrounding the first and second active regions and being of conductivity type different from that of the first active regions; and

drain regions formed at n+ junctions of both end portions of the first active regions.

31. (NEW) A multi-finger type ESD protection device comprising:

a semiconductor substrate;

a plurality of first active regions formed separately on the semiconductor substrate;

a plurality of gates formed in each of the first active regions;

at least one second active region of a predetermined conductive type, formed between the first active regions, wherein the predetermined conductive type second active region includes a p+ junction connected to ground Vss; and

a third active region surrounding the first and second active regions and being of conductivity type different from that of the first active regions,

wherein spaces are provided between the first and second active regions.--